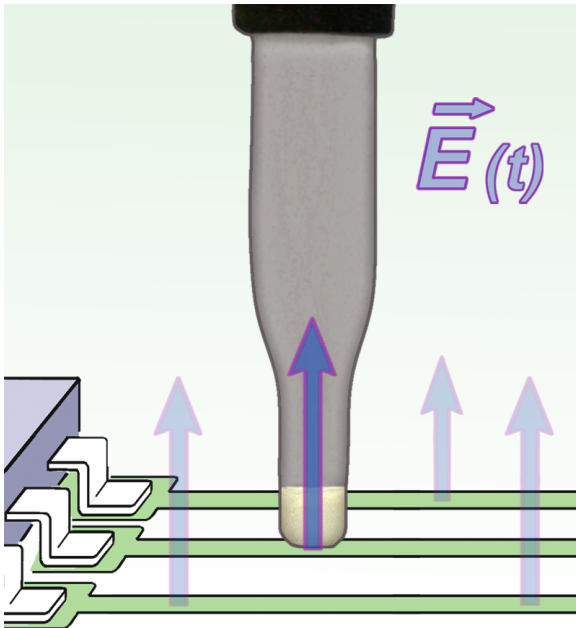


# XFS-E 10

Scanner Probe 30 MHz up to 6 GHz



## Short description

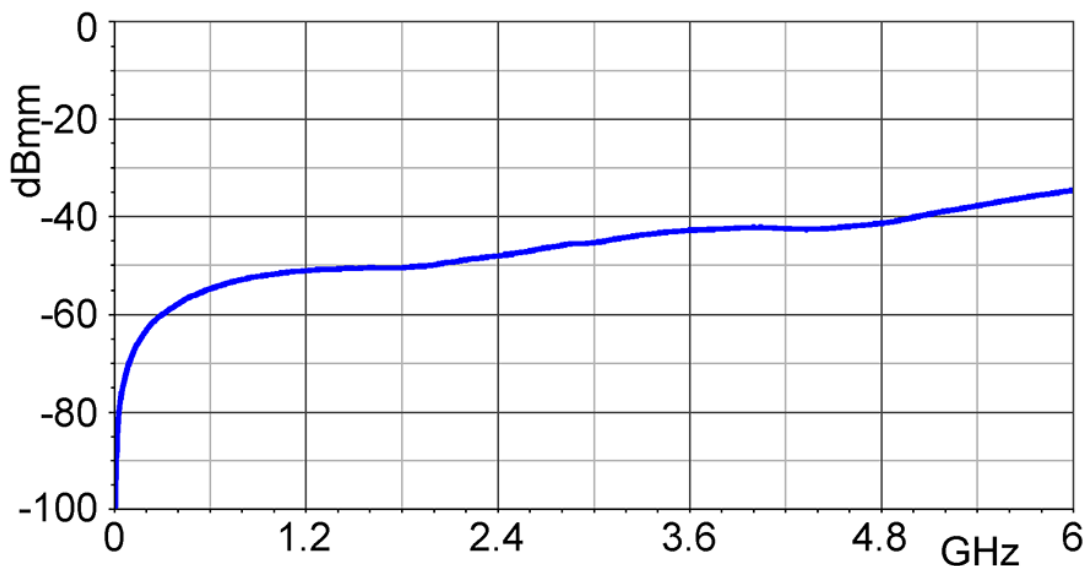
The electrode in the probe head of the XFS-E 10 scanner probe has a width of approx. 0.2 mm. With the probe even smallest E-field sources can be located, e.g. conducting paths with a width of 0.1 mm or single pins on multi pinned ICs. To measure, the E-field probe is positioned onto the object.

The XFS-E 10 probe is a passive near-field probe. Normally the probe head is positioned directly onto the measured object (high electric field strength). It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field scanner probe has an internal terminating resistance.

## Technical parameters

Frequency range	30 MHz ... 6 GHz
Resolution	$\approx 0.2$ mm
Probe head dimensions	$\approx (0.5 \times 2)$ mm
Connector - output	SMA, male, jack

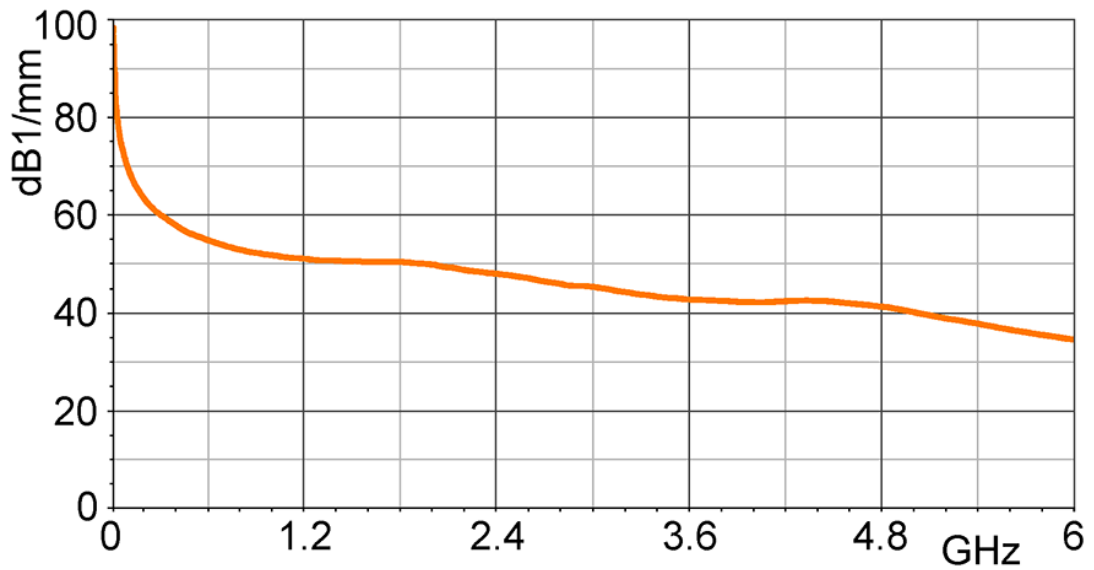
Frequency response [dB $\mu$ V] / [dB $\mu$ A/m]



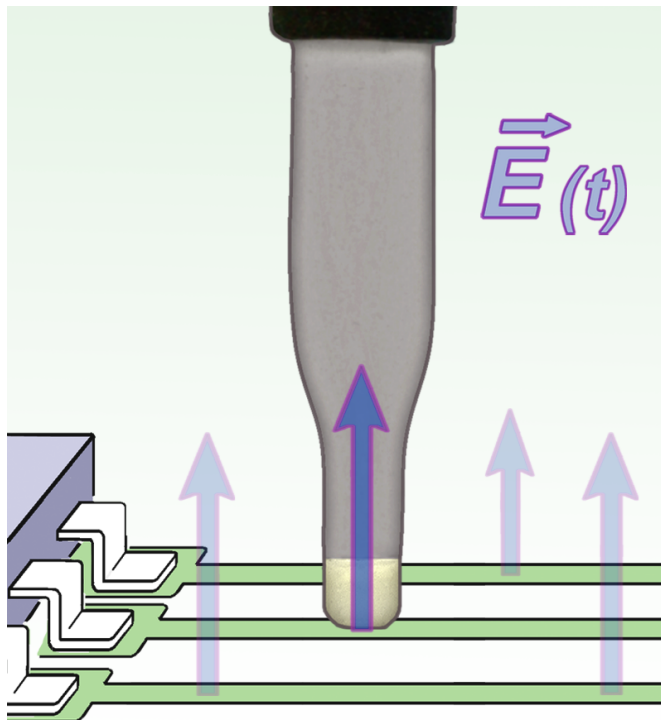
# XFS-E 10

Scanner Probe 30 MHz up to 6 GHz

E- field correction curve [dB $\mu$ V/mm] / [dB $\mu$ V]



Measuring principles



# XFS-E 10

Scanner Probe 30 MHz up to 6 GHz

**LANGER**  
EMV-Technik

